



INTERNATIONAL ATOMIC ENERGY AGENCY
UNITED NATIONS EDUCATIONAL, SCIENTIFIC AND CULTURAL ORGANIZATION



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SPRING COLLEGE ON AMORPHOUS SOLIDS
AND THE LIQUID STATE

14 April - 18 June 1982

OPTICAL SPECTROSCOPY AND PHOTOELECTRON SPECTROSCOPY
OF AMORPHOUS SEMICONDUCTORS

(Part I)

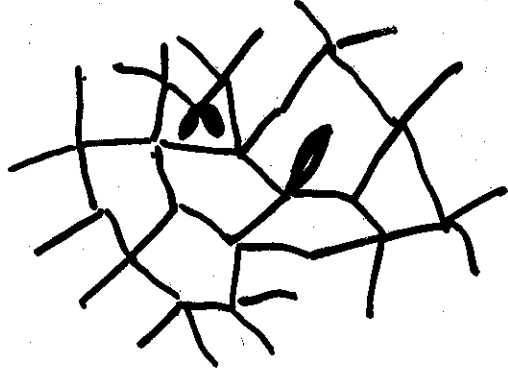
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These are preliminary lecture notes, intended only for distribution to participants.
Missing or extra copies are available from Room 230.

Materials Discussed:

Amorphous Semiconductors with
Optoelectronic Applications: Ge, Si

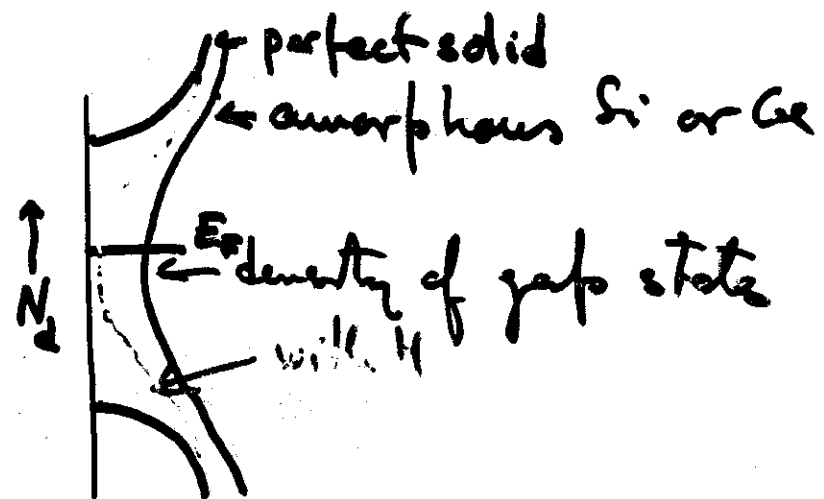
Random tetrahedral network



length fluctuates
by $\sim 1\%$
Bond angles
by $\sim 10\%$

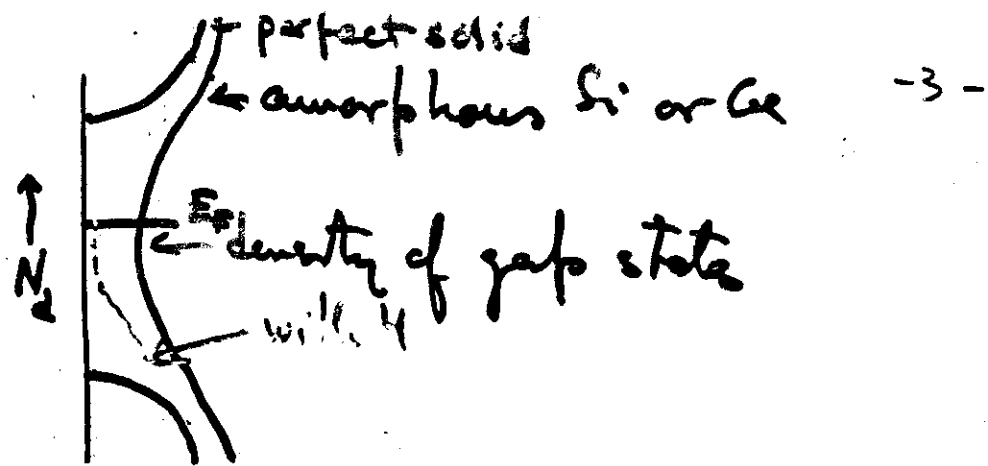
Dangling bands

Dangling bands produce
strong density of states in the
gap $\sim 10^{20} - 10^{21} / \text{eV cm}^3$



Under these conditions the material
behaves as metallic and cannot
be doped with group V
elements (donors) or group III (acceptors).

Solution: Saturate the
dangling bonds with either
hydrogen (atomic) or with
fluorine (possibly also chlorine)



Under these conditions the material behaves as metallic and cannot be doped with group V elements (donors) or group III (acceptors).

Solution : Saturate the dangling bonds with either hydrogen (atomic) or with fluorine (possibly also chlorine)

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The level which was in the middle of the gap moves down to about -5 eV from top of valence band for H, ~ -8 for fluorine and the gap is cleaned up. Doping becomes possible.

Preparation techniques

Vacuum deposition

Sputtering of a Si (Ge) target
in Ar + $\begin{cases} (+I) \\ (SiF_4) \end{cases} + \begin{cases} PH_3 (n-type) \\ B_2H_6 (p-type) \end{cases}$

Contents of the Lecture.

Study of vibrational spectra
of $\text{Si}(\text{H})$, (F) and $\text{Si}(\text{H})$ doped
with P or B.

Study of electronic states
in these materials.

Methods: Spectroscopy

Vibrational Spectroscopy (non-stimulated)

IR, Raman, HyperRaman,
Brillouin

General principles, selection
rules for solids, molecules,
amorphous materials: Parity
Raman tensor.

Cross Section

Resonance phenomena

Intrinsic spectra of $\alpha\text{-Si}(\text{a.c.})$
Spectra of defects
(H, F, B, P.....)

Detailed discussion of
the vibrations of Si-H bands.

Photoelectron Spectroscopy

General Principles and
Experimental methods:

Synchrotron radiation spectroscopy

Fermi Energies and Density of States
Valence bands

Gap States: Threshold spectroscopy

Intrinsic spectra of a-Si(a-G)
Spectra of defects -7-
(H, F, B, P.....)

Detailed discussion of
the vibrations of Si-H bonds.

Photoelectron Spectroscopy

General Principles and
Experimental methods:

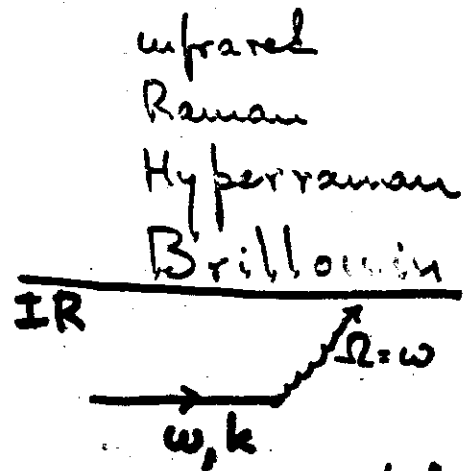
Synchrotron radiation spectroscopy

Fermi Energies and Density
Valence bands

Gap State: Threshold spectroscopy

-8-
Core levels: charge fluctuations
in a-Si
Impurities, Fluorine, hydrogen
...

Vibrational Spectroscopy



Two types of instruments:

Gratings - Prisms $\sim 500 \text{ cm}^{-1}$

Fourier - Transform $\sim 50 \text{ cm}^{-1}$

Remember that

$$\frac{\text{Wavenumbers}(\text{cm}^{-1})}{1/\lambda} \times 1.24 \times 10^{-4} = \text{eV}$$

Selection rules:

In solids (crystalline) k is conserved
to a reciprocal lattice vector,

-9- hence

$$q(\text{excitation}) = k + G \quad -10^{-7}$$

$G=0$ if we stay in the

first Brillouin zone (reduced zone scheme). We only see phonons of $q \approx 0$ since

$$k = \frac{2\pi}{\lambda} \ll \frac{2\pi}{a_0} \quad \left(\begin{array}{l} \text{size of} \\ \text{Brillouin zone} \end{array} \right)$$

$\lambda \sim 10^{-4} \text{ cm}$ $a_0 \sim 10^{-8} \text{ cm}$

Parity selection rule:

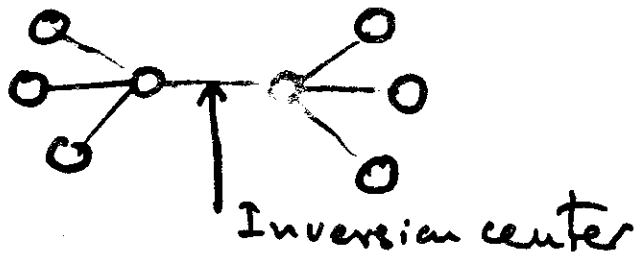
If solid or molecule has inversion symmetry, eigenstates have definite parity, i.e., they are odd or even upon inversion.

Photon is odd (vector, electric field) hence couples only to odd excitations

Examples

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Si crystal



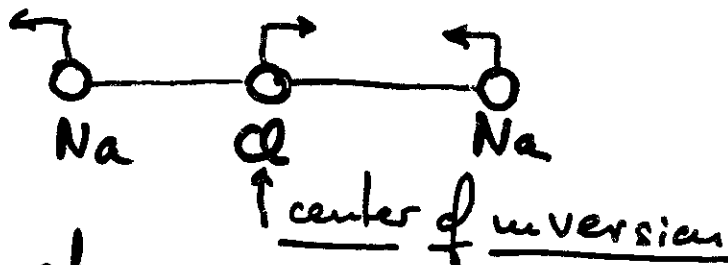
Optical phonons

at $q=0$

are even hence ir-forbidden

Material transparent in ir:
used as windows and substrate.

NaCl



phonon at $q=0$ reverses sign
upon inversion, hence odd
and ir-allowed.

$$\langle f | \hat{e} \cdot \underline{p} | 0 \rangle = \langle f | \hat{e} \cdot \underline{M} | 0 \rangle$$

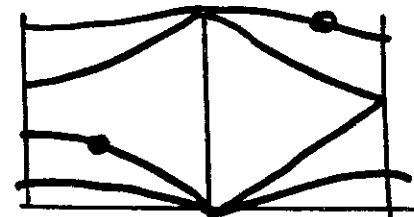
must be $\ominus$

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It is possible to couple also
to two or more excitations
(phonons):

$$\omega, k \quad \Omega_1, q_1 \quad \Omega_2, q_2 \quad \omega = \Omega_1 \pm \Omega_2$$

$$k = q_1 \pm q_2$$



$q_1 + q_2 = 0$
but not $q_1 = 0$

In this manner it is in
principle possible to
see all phonons, not
only $q=0$

Absorption measured
by absorption coefficient (cm^{-1})

$$I = I_0 e^{-\alpha x}$$

$\alpha \approx 10^5 \text{ cm}^{-1}$ for 1 phonon allowed
 $\alpha \approx 10$ for 2 phonons.

relationship between α and ϵ 12
 $\alpha = \frac{4\pi\kappa}{\lambda}$ $\kappa = \text{imag. part of ref. index}$

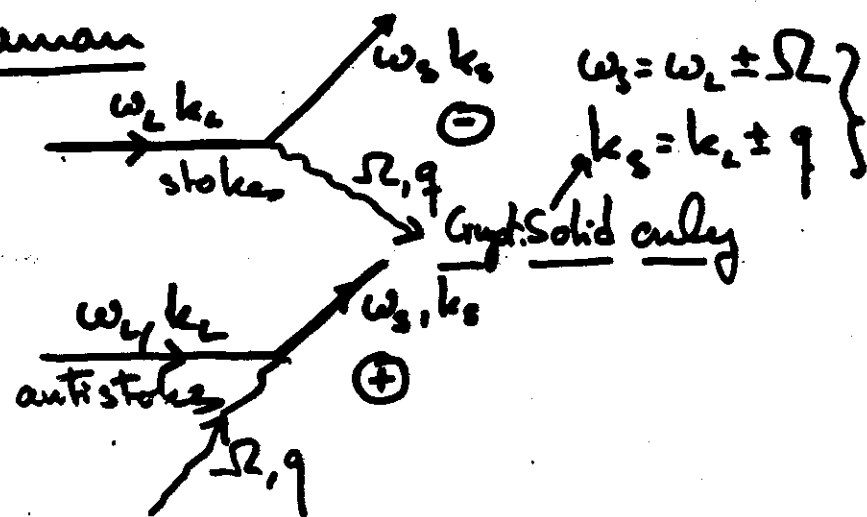
$$n^2 - \kappa^2 = \epsilon_1$$

$$2n\kappa = \epsilon_2$$

$$\epsilon = \epsilon_1 + i\epsilon_2$$

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Raman



Parity selection rules:

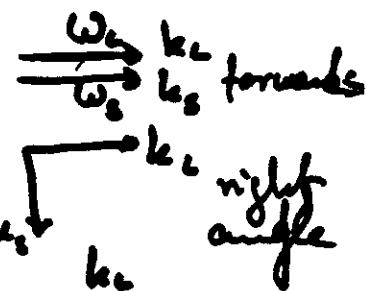
Now two photons hence:

Raman couples only to even excitations. If parity is good $q. u.$:

Raman allowed $\equiv$ if forbidden
 (within dipole approximation)

Solid k -selection rule (crystal, not amorphous) 13
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$$k_s = k_L \pm q$$



$$\Delta k = q \lesssim \frac{4\pi}{\lambda} \approx 0$$

hence also we only couple to $q \approx 0$

Comparison with neutron scattering
thermal neutrons

$$E \approx 0.02 \text{ eV} = \frac{\hbar^2 q^2}{2M}$$

calculation in Hartree (atomic units)
 $\hbar = 1$ $M = 1800$

$$E = \frac{0.02}{27} \text{ Hartree} = \frac{1}{2M} q^2$$

$$q = 2 \text{ at units / Brillouin zone} \approx \frac{2\pi}{a} \approx 0.6$$

Neutron scattering expensive cumbersome and not accurate for frequencies (not better than 1 cm^{-1}) Raman $\sim 1 \text{ cm}^{-1}$

Typical Raman Efficiencies

In solids are talks about efficiencies $dS/d\Omega$, per cm and steradian

For optical mode of crystal Si at $\sim 2 \text{ eV} = \omega_L$:

$$\frac{dS}{d\Omega} \approx 2 \times 10^{-7} \text{ sr}^{-1} \text{ cm}^{-1}$$

Hence since absorption coefficient at $\omega_L \propto 10^4 \text{ cm}^{-1}$

$$\frac{dS}{d\Omega} \times L = 2 \times 10^{-7} \times 10^{-4} = \underline{\underline{2 \times 10^{-11} \text{ sr}^{-1}}}$$

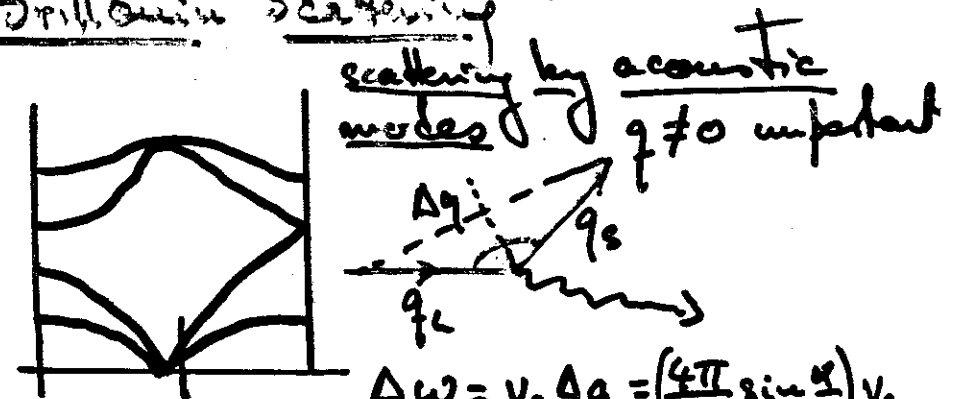
very small.

Hard to detect unless very good

spectrometers using a very high-stray light rejection are used. (stray light $\equiv$ elastically (Rayleigh) scattered light)

One uses double or triple monochromators and photomultipliers with photon counting.

Brillouin Scattering



$$\Delta\omega = v_s \Delta q = \left(\frac{4\pi}{\lambda} \sin \frac{\theta}{2} \right) v_s$$

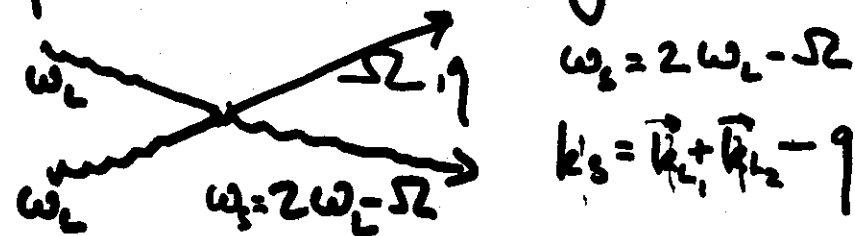
In principle it helps you find v_s , i.e., the elastic constants. Interesting for a-Si

Techniques

Fabry - Perot interferometers with
multiple pass (up to 5x):

J. Sandercock

Think by yourselves about selection
rules, especially parity (always odd)

Hyperraman scatteringParity selection rule

Same as for IR scattering
Hyperraman couples to odd excitations.

But it can couple to
silent modes, forbidden by symmetry
other than inversion.

